



Page 1 of 5

An IS/ISO 9002 and IECQ Certified Manufacturer

#### PNP SILICON PLANAR EPITAXIAL TRANSISTORS

BC559, B, C BC560, B, C TO-92 Plastic Package

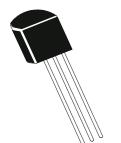


## **Low Noise Transistors**

# ABSOLUTE MAXIMUM RATINGS(Ta=25 deg C unless otherwise specified)

DESCRIPTION	SYMBOL	BC559	BC560	UNITS		
Collector Emitter Voltage	V <sub>CEO</sub>	30	45	V		
Collector Base Voltage	V <sub>CBO</sub>	30	50	V		
Emitter Base Voltage	V <sub>EBO</sub>	5	5	V		
Collector Current Continuous	I <sub>C</sub>	100	100			
Power Dissipation@ Tc=25 degC	P <sub>D</sub>	625	mW			
Derate Above 25 deg C		5	mW/ ºC			
Power Dissipation@ Tc=25 degC	P <sub>D</sub>	1.5	W			
Derate Above 25 deg C		12	mW/ ºC			
Operating And Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +	°C			
THERMAL RESISTANCE						
Junction to ambient	R <sub>th(j-a)</sub>	200		°C/W		
Junction to case	R <sub>th(j-c)</sub>	83.3	°C/W			

#### PNP SILICON PLANAR EPITAXIAL TRANSISTORS

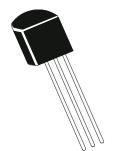


BC559, B, C BC560, B, C TO-92 Plastic Package

# **ELECTRICAL CHARACTERISTICS (Ta=25 deg C Unless Otherwise Specified)**

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Collector Emitter Voltage						
BC559	$V_{CEO}$	$I_C=10$ mA, $I_B=0$	30			V
BC560			45			V
Collector Base Voltage						
BC559		$I_C=10uA, I_E=0$	30			V
BC560			50			V
Emitter Base Voltage	$V_{EBO}$	$I_E=10uA, I_C=0$	5			V
Collector Cut off Current	I <sub>CBO</sub>	$V_{CB} = 30V, I_{E} = 0$			15	nA
		$V_{CB} = 30V, I_{E} = 0$			5	uA
		T <sub>a</sub> = +125 deg C				
Emitter Cut off Current	I <sub>EBO</sub>	$V_{CE}=4V, I_{C}=0$			15	nA
DC Current Gain						
В		V <sub>CE</sub> =5V,I <sub>C</sub> =10uA	100			
С			100			
В		$V_{CE}=5V,I_{C}=2mA$	180		460	
С			380		800	
BC559, BC560			120		800	
Callactor Fruittor Saturation Valtage						
Collector Emitter Saturation Voltage	\/	_10m\			0.05	V
	V <sub>CE(sat)</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0.5mA	•		0.25	-
		I <sub>C</sub> =100mA,I <sub>B</sub> =see note	l		0.6	V
		I <sub>C</sub> =100mA,I <sub>B</sub> =5mA*		0.25		V
DECORPTION	0)/145.01	TEGT CONSTITUTE		T. (5)	84437	
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Base Emitter Saturation Voltage	\/	$I_C=100$ mA, $I_B=5$ mA*		1.1		V
Dase Ellitter Saturation voitage	V <sub>BE(sat)</sub>	IC- IOOIIIA,IB=OIIIA		1.1		V
Base Emitter On Voltage	\/	I <sub>C</sub> =10uA,V <sub>CE</sub> =5V		0.52		V
Dase Ellitter On voltage	V <sub>BE(on)</sub>	$I_C=100uA, V_{CE}=5V$ $I_C=100uA, V_{CE}=5V$		0.52		V
		$I_C=100uA, V_{CE}=5V$ $I_C=2mA, V_{CE}=5V$	0.55	0.55	0.70	V
		IC-ZIIIA, V CE=5 V	บ.ออ		0.70	V

## PNP SILICON PLANAR EPITAXIAL TRANSISTORS

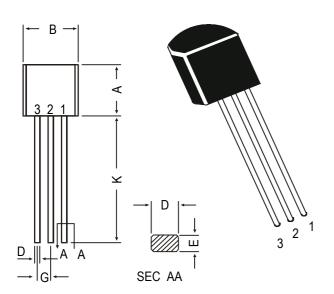


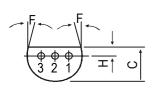
BC559, B, C BC560, B, C TO-92 Plastic Package

# **ELECTRICAL CHARACTERISTICS (Ta=25 deg C Unless Otherwise Specified)**

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
DYNAMICS CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	$I_C=10$ mA, $V_{CE}=5$ V				
		f=100MHz		250		MHz
Collector Base Capacitance	C <sub>cbo</sub>	$V_{CB} = 10V, I_{E} = 0,$		2.5		pF
		f =1MHz				
Noise Figure	NF <sub>1</sub>	V <sub>CE</sub> =5V,I <sub>C</sub> =200uA			2.0	dB
		$R_S=2K\Omega, f=30H_Z$ To				
		15KHz				
	NF <sub>2</sub>	$V_{CE} = 5V, I_{C} = 200uA$			10	dB
		$R_S=100K\Omega, f=1.0KH_Z$				
		f=200Hz				
Small Signal Current Gain						
В	lh <sub>fe</sub> l	$V_{CE} = 5V, I_{C} = 2mA$	240		500	
С		f=1kH <sub>Z</sub>	450		900	

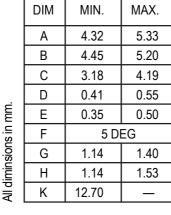
## **TO-92 Plastic Package**



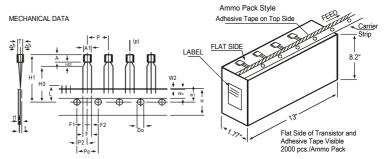


PIN CONFIGURATION 1. COLLECTOR

- 2. BASE
- 3. EMITTER



#### **TO-92 Transistors on Tape and Ammo Pack**



#### All dimensions in mm unless specified otherwise

ITEM.			SPECIF	ICATIO	N		
ITEM	SYMBOL	MIN.	NOM.	OM. MAX. TOL.		REMARKS	
BODY WIDTH	A1	4.0		4.8			
BODY HEIGHT	A	4.8		5.2 4.2			
BODY THICKNESS PITCH OF COMPONENT	T P	3.9	12.7	4.2	±1		
FEED HOLE PITCH	Po		12.7		±0.3	CUMULATIVE PITCH ERROR 1.0 mm/20	
FEED HOLE CENTRE TO COMPONENT CENTRE	P2		6.35		±0.4	PITCH TO BE MEASURED AT BOTTOM OF CLINCH	
DISTANCE BETWEEN OUTER					+0.6		
LEADS	F		5.08	1	-0.2	AT TOD OF DODY	
COMPONENT ALIGNMENT TAPE WIDTH	∆h W		0 18	l '	±0.5	AT TOP OF BODY	
HOLD-DOWN TAPE WIDTH	Wo		6		±0.2		
HOLE POSITION	W1		9		+0.7 -0.5		
HOLD-DOWN TAPE POSITION			0.5		±0.2		
LEAD WIRE CLINCH HEIGHT	Ho		16	ا مم مح	±0.5		
COMPONENT HEIGHT LENGTH OF SNIPPED LEADS	H1 I			23.25 11.0			
FEED HOLE DIAMETER	Do l		4	' ' '	±0.2		
TOTAL TAPE THICKNESS	ť			1.2		t1 0.3 - 0.6	
LEAD - TO - LEAD DISTANCEF1,	F2		2.54		+0.4 -0.1		
CLINCH HEIGHT	H2			3	-0.1		
PULL - OUT FORCE	(P)	6N					

- NOTES

  1. MAXIMUM ALIGNMENT DEVIATION BETWEEN LEADS NOT TO BE GREATER THAN 0.2 mm.
  2. MAXIMUM NON-CUMULATIVE VARIATION BETWEEN TAPE FEED HOLES SHALL NOT EXCEED 1 mm IN 20
- PITCHES.
  HOLDDOWN TAPE NOT TO EXCEED BEYOND THE EDGE(S) OF CARRIER TAPE AND THERE SHALL BE NO
- EXPOSURE OF ADHESIVE.

  4. NO MORE THAN 3 CONSEQUTIVE MISSING COMPONENTS ARE PERMITTED.

  5. A TAPE TRAILER, HAVING AT LEAST THREE FEED HOLES ARE REQUIRED AFTER THE LAST COMPONENT.

  6. SPLICES SHALL NOT INTERFERE WITH THE SPROCKET FEED HOLES.

## **Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details Net Weight / Qty		Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk	1K/polybag	200 gm/1K pcs	3"x 7.5"x 7.5"	5.0K	17" x 15" x 13.5"	80.0K	23 kgs
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2.0K	17" x 15" x 13.5"	32.0K	12.5 kgs

**Notes** 

BC559, B, C BC560, B, C TO-92 Plastic Package

#### **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of
Continental Device India Limited
C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290
e-mail sales@cdil.com www.cdil.com